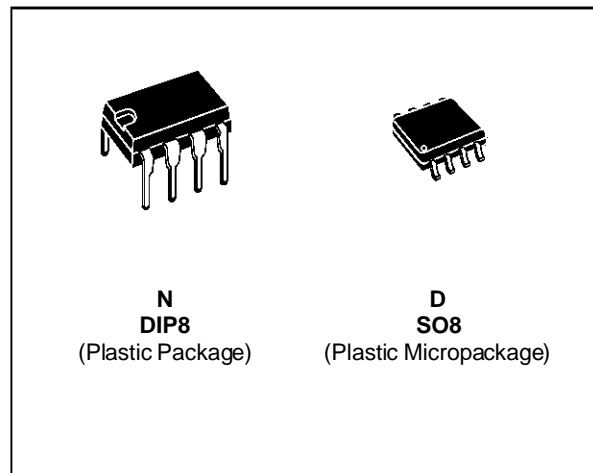


**WIDE BANDWIDTH
DUAL J-FET OPERATIONAL AMPLIFIERS**

- LOW POWER CONSUMPTION
- WIDE COMMON-MODE (UP TO V_{CC}^+) AND DIFFERENTIAL VOLTAGE RANGE
- LOW INPUT BIAS AND OFFSET CURRENT
- OUTPUT SHORT-CIRCUIT PROTECTION
- HIGH INPUT IMPEDANCE J-FET INPUT STAGE
- INTERNAL FREQUENCY COMPENSATION
- LATCH UP FREE OPERATION
- HIGH SLEW RATE : $16V/\mu s$ (typ)



DESCRIPTION

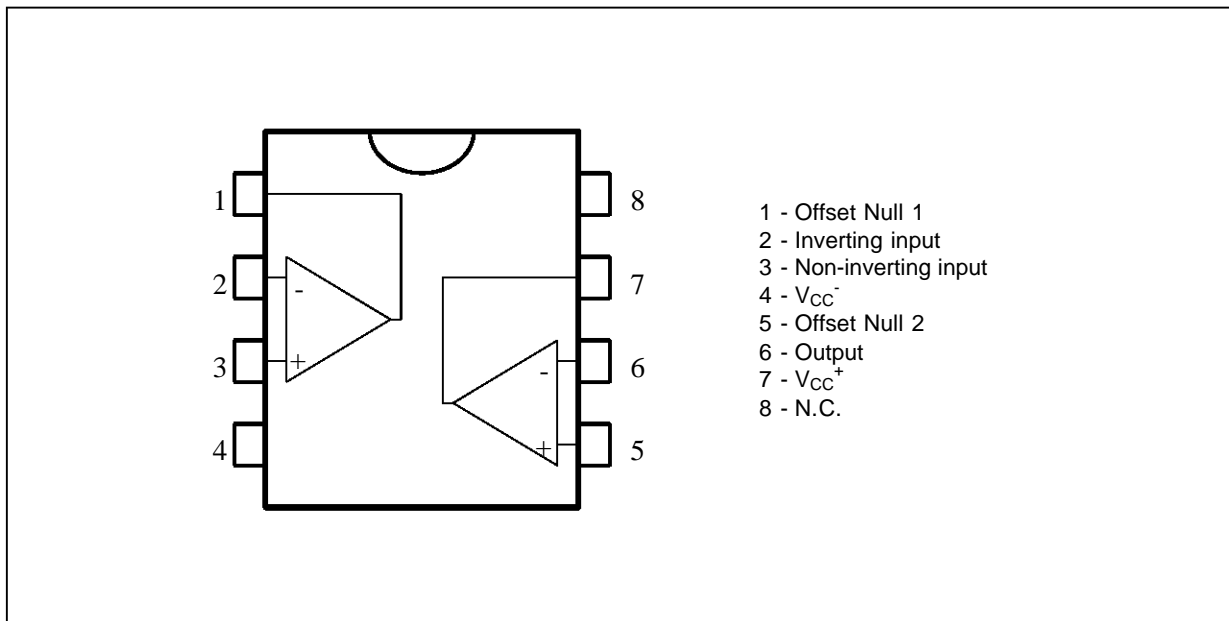
The LF353 are high speed J-FET input dual operational amplifiers incorporating well matched, high voltage J-FET and bipolar transistors in a monolithic integrated circuit.

The devices feature high slew rates, low input bias and offset currents, and low offset voltage temperature coefficient.

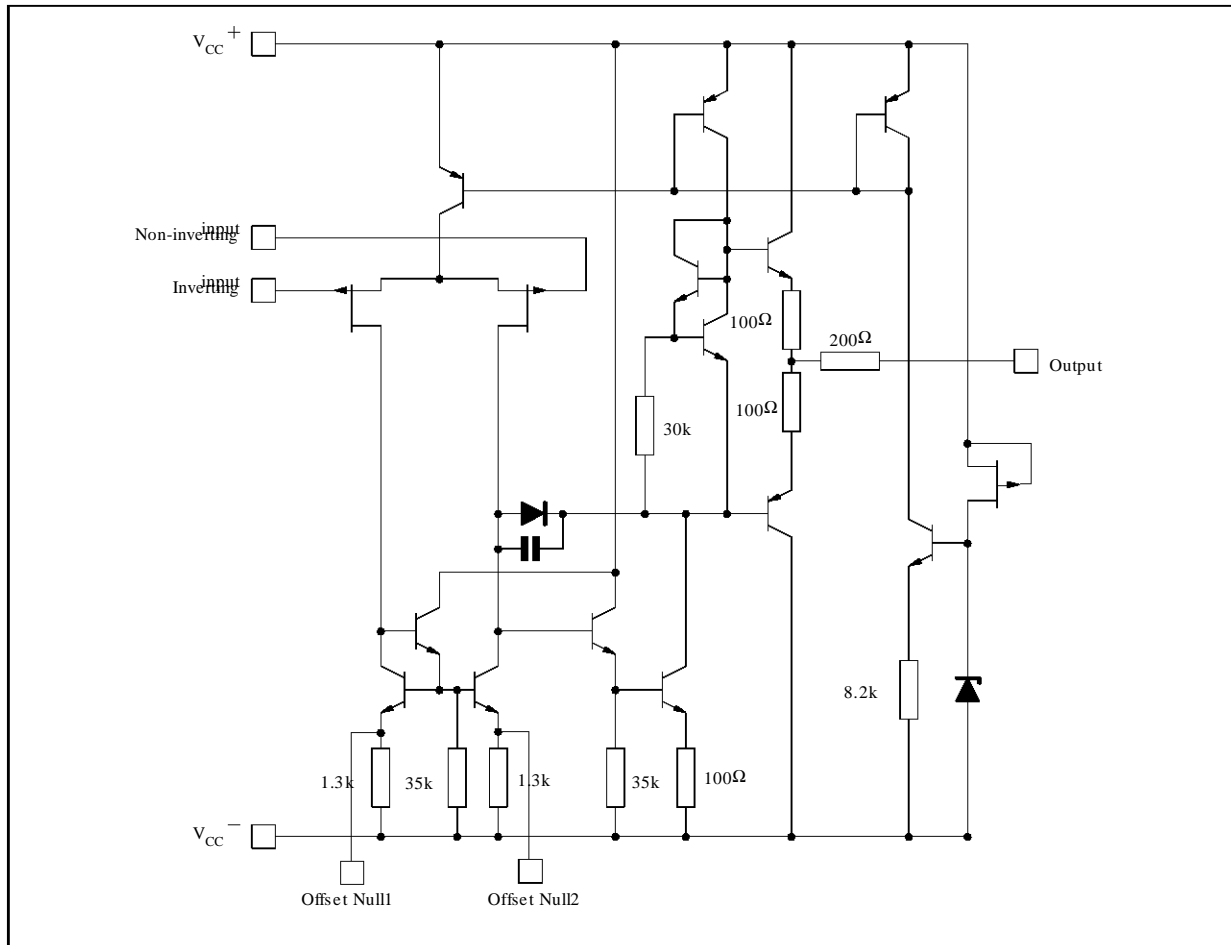
ORDER CODES

Part Number	Temperature	Package	
		N	D
LF353	0°C, +70°C	•	•
LF253	-40°C, +105°C	•	•
LF153	-55°C, +125°C	•	•

PIN CONNECTIONS (top view)



SCHEMATIC DIAGRAM (each amplifier)



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CC}	Supply Voltage - (note 1)	± 18	V
V_i	Input Voltage - (note 3)	± 15	V
V_{id}	Differential Input Voltage - (note 2)	± 30	V
P_{tot}	Power Dissipation	680	mW
	Output Short-circuit Duration - (note 4)	Infinite	
T_{oper}	Operating Free Air Temperature Range	LF353 LF253 LF153	$^{\circ}C$
T_{stg}	Storage Temperature Range	-65 to 150	$^{\circ}C$

- Notes :**
1. All voltage values, except differential voltage, are with respect to the zero reference level (ground) of the supply voltages where the zero reference level is the midpoint between V_{CC}^+ and V_{CC}^- .
 2. Differential voltages are at the non-inverting input terminal with respect to the inverting input terminal.
 3. The magnitude of the input voltage must never exceed the magnitude of the supply voltage or 15 volts, whichever is less.
 4. The output may be shorted to ground or to either supply. Temperature and /or supply voltages must be limited to ensure that the dissipation rating is not exceeded.

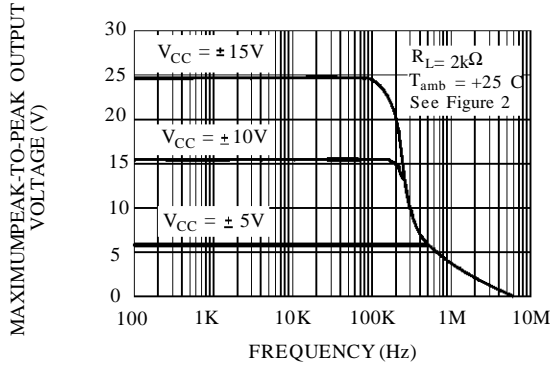
ELECTRICAL CHARACTERISTICS

V_{CC} = ±15V, T_{amb} = 25°C (unless otherwise specified)

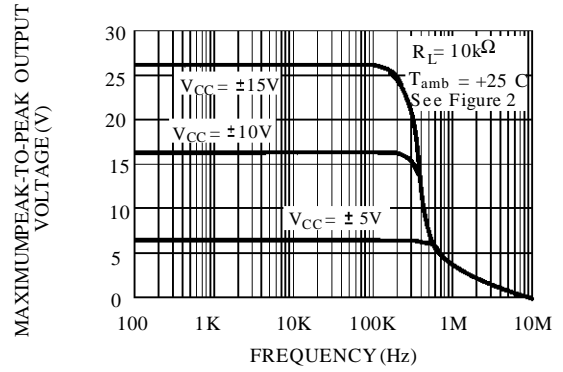
Symbol	Parameter	LF153 - LF253 - LF353			Unit
		Min.	Typ.	Max.	
V _{io}	Input Offset Voltage (R _S = 10kΩ) T _{amb} = 25°C T _{min.} ≤ T _{amb} ≤ T _{max.}		3	10 13	mV
DV _{io}	Input Offset Voltage Drift		10		μV/°C
I _{io}	Input Offset Current * T _{amb} = 25°C T _{min.} ≤ T _{amb} ≤ T _{max.}		5	100 4	pA nA
I _{ib}	Input Bias Current * T _{amb} = 25°C T _{min.} ≤ T _{amb} ≤ T _{max.}		20	200 20	pA nA
A _{vd}	Large Signal Voltage Gain (R _L = 2kΩ, V _O = ±10V) T _{amb} = 25°C T _{min.} ≤ T _{amb} ≤ T _{max.}	50 25	200		V/mV
SVR	Supply Voltage Rejection Ratio (R _S = 10kΩ) T _{amb} = 25°C T _{min.} ≤ T _{amb} ≤ T _{max.}	80 80	86		dB
I _{CC}	Supply Current (no load) T _{amb} = 25°C T _{min.} ≤ T _{amb} ≤ T _{max.}		1.4	3.2 3.2	mA
V _{icm}	Input Common Mode Voltage Range	±11	+15 -12		V
CMR	Common Mode Rejection Ratio (R _S = 10kΩ) T _{amb} = 25°C T _{min.} ≤ T _{amb} ≤ T _{max.}	70 70	86		dB
I _{OS}	Output Short-circuit Current T _{amb} = 25°C T _{min.} ≤ T _{amb} ≤ T _{max.}	10 10	40	60 60	mA
±V _{OPP}	Output Voltage Swing T _{amb} = 25°C T _{min.} ≤ T _{amb} ≤ T _{max.}				V
				R _L = 2kΩ R _L = 10kΩ R _L = 2kΩ R _L = 10kΩ	
SR	Slew Rate (V _i = 10V, R _L = 2kΩ, C _L = 100pF, T _{amb} = 25°C, unity gain)	12	16		V/μs
t _r	Rise Time (V _i = 20mV, R _L = 2kΩ, C _L = 100pF, T _{amb} = 25°C, unity gain)		0.1		μs
K _{OV}	Overshoot (V _i = 20mV, R _L = 2kΩ, C _L = 100pF, T _{amb} = 25°C, unity gain)		10		%
GBP	Gain Bandwidth Product (f = 100kHz, T _{amb} = 25°C, V _{in} = 10mV, R _L = 2kΩ, C _L = 100pF)	2.5	4		MHz
R _i	Input Resistance		10 ¹²		Ω
THD	Total Harmonic Distortion (f = 1kHz, A _V = 20dB, R _L = 2kΩ, C _L = 100pF, T _{amb} = 25°C, V _O = 2V _{PP})		0.01		%
e _n	Equivalent Input Noise Voltage (f = 1kHz, R _S = 100Ω)		15		$\frac{nV}{\sqrt{Hz}}$
∅ _m	Phase Margin		45		Degrees
V _{O1} /V _{O2}	Channel Separation (A _V = 100, T _{amb} = 25°C)		120		dB

* The input bias currents are junction leakage currents which approximately double for every 10°C increase in the junction temperature.

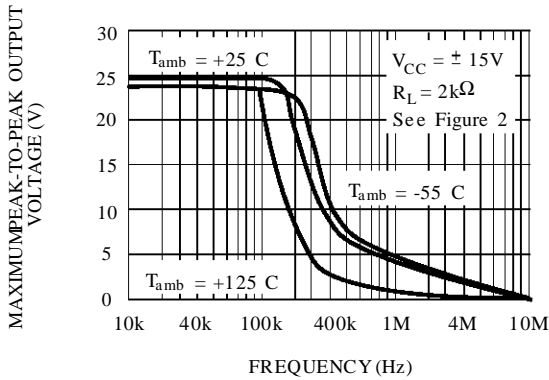
MAXIMUM PEAK-TO-PEAK OUTPUT VOLTAGE VERSUS FREQUENCY



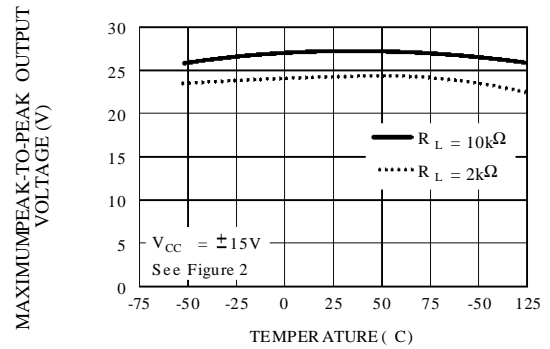
MAXIMUM PEAK-TO-PEAK OUTPUT VOLTAGE VERSUS FREQUENCY



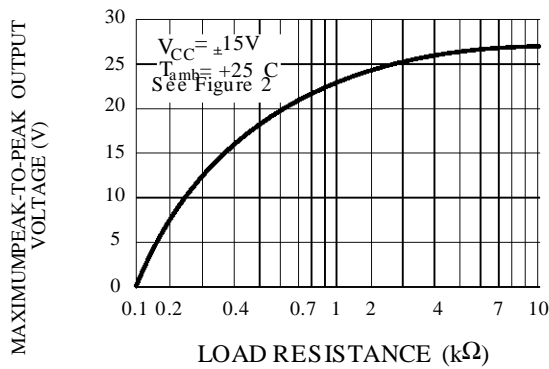
MAXIMUM PEAK-TO-PEAK OUTPUT VOLTAGE VERSUS FREQUENCY



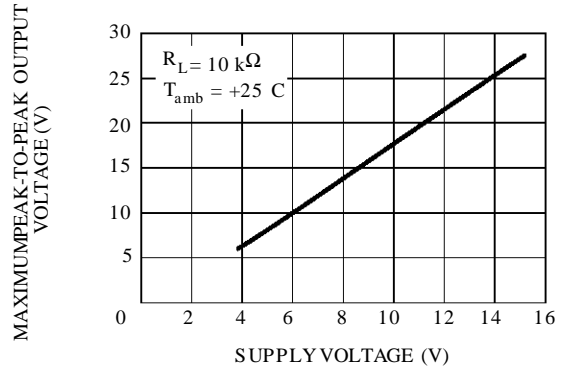
MAXIMUM PEAK-TO-PEAK OUTPUT VOLTAGE VERSUS FREE AIR TEMP.



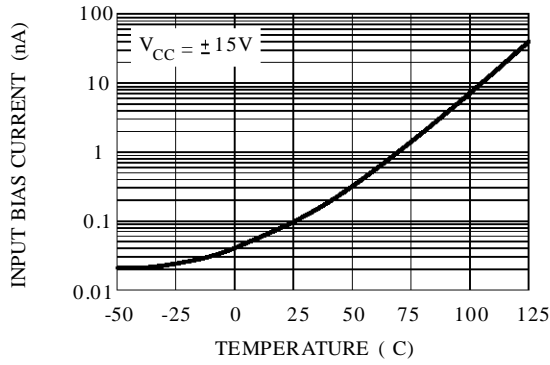
MAXIMUM PEAK-TO-PEAK OUTPUT VOLTAGE VERSUS LOAD RESISTANCE



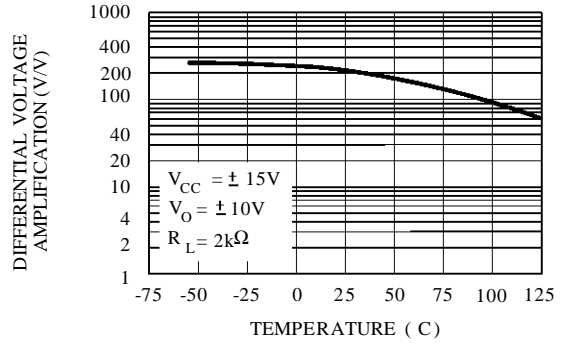
MAXIMUM PEAK-TO-PEAK OUTPUT VOLTAGE VERSUS SUPPLY VOLTAGE



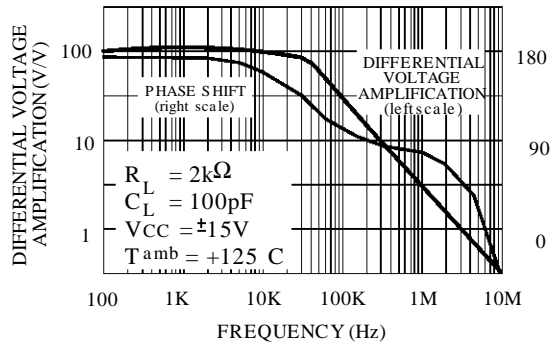
INPUT BIAS CURRENT VERSUS FREE AIR TEMPERATURE



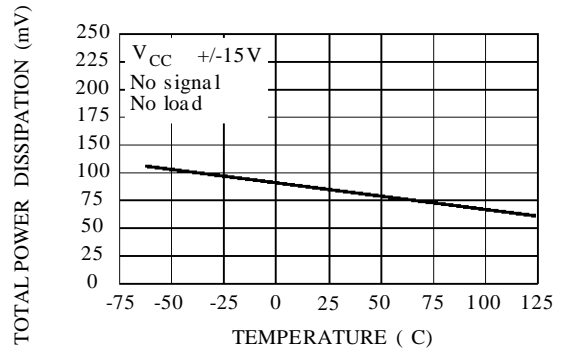
LARGE SIGNAL DIFFERENTIAL VOLTAGE AMPLIFICATION VERSUS FREE AIR TEMPERATURE



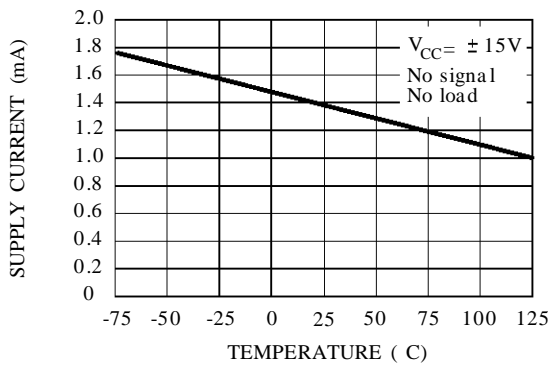
LARGE SIGNAL DIFFERENTIAL VOLTAGE AMPLIFICATION AND PHASE SHIFT VERSUS FREQUENCY



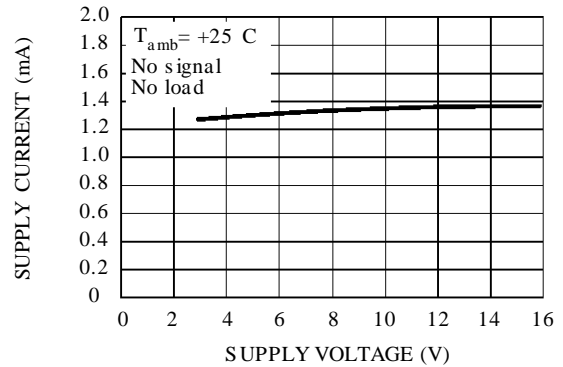
TOTAL POWER DISSIPATION VERSUS FREE AIR TEMPERATURE



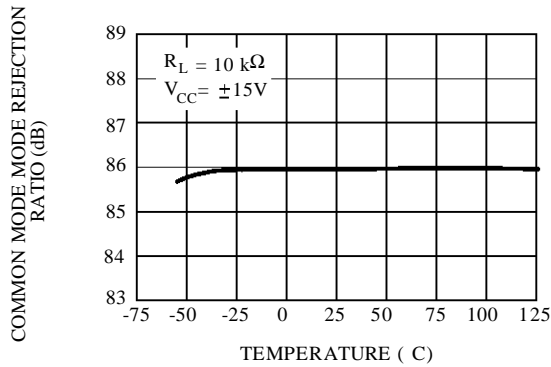
SUPPLY CURRENT PER AMPLIFIER VERSUS FREE AIR TEMPERATURE



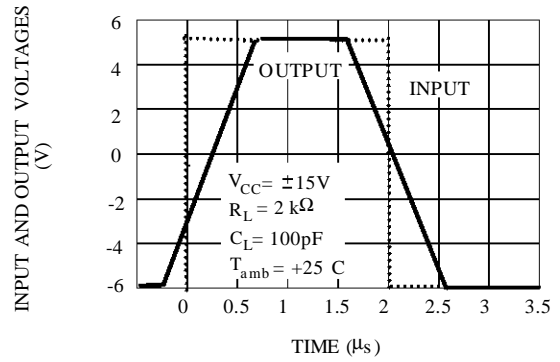
SUPPLY CURRENT PER AMPLIFIER VERSUS SUPPLY VOLTAGE



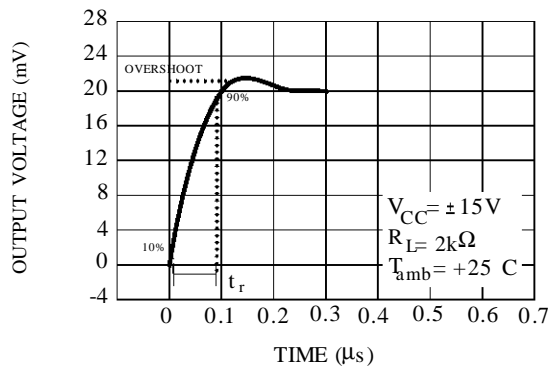
**COMMON MODE REJECTION RATIO
VERSUS FREE AIR TEMPERATURE**



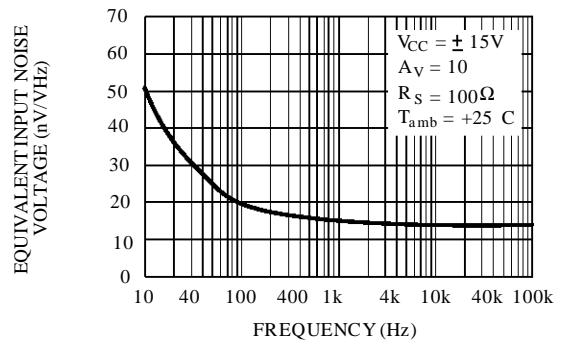
**VOLTAGE FOLLOWER LARGE SIGNAL
PULSE RESPONSE**



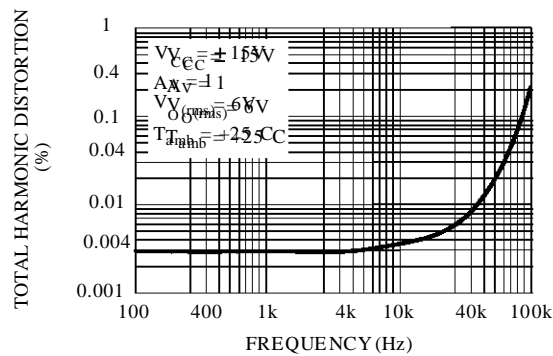
**OUTPUT VOLTAGE VERSUS
ELAPSED TIME**



**EQUIVALENT INPUT NOISE VOLTAGE
VERSUS FREQUENCY**



**TOTAL HARMONIC DISTORTION VERSUS
FREQUENCY**



PARAMETER MEASUREMENT INFORMATION

Figure 1 : Voltage Follower

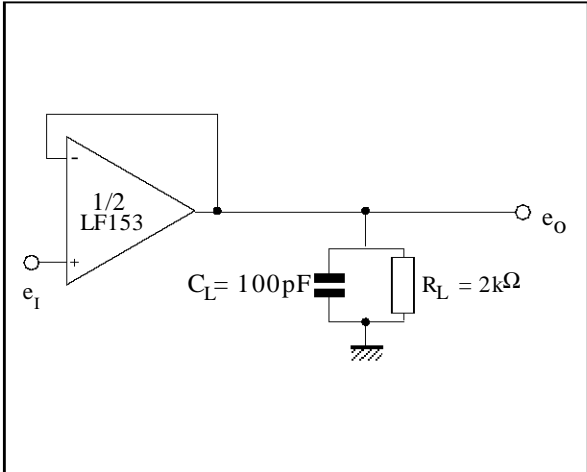
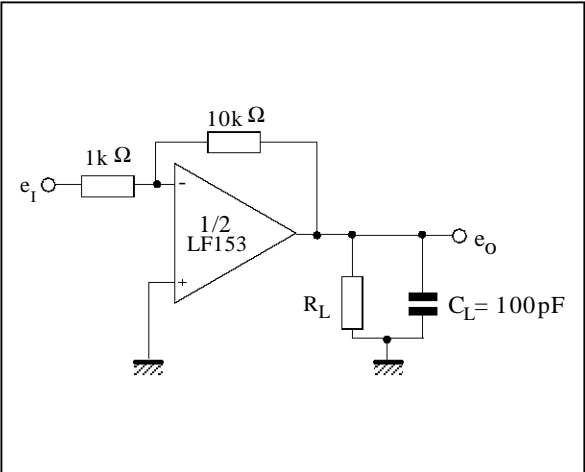
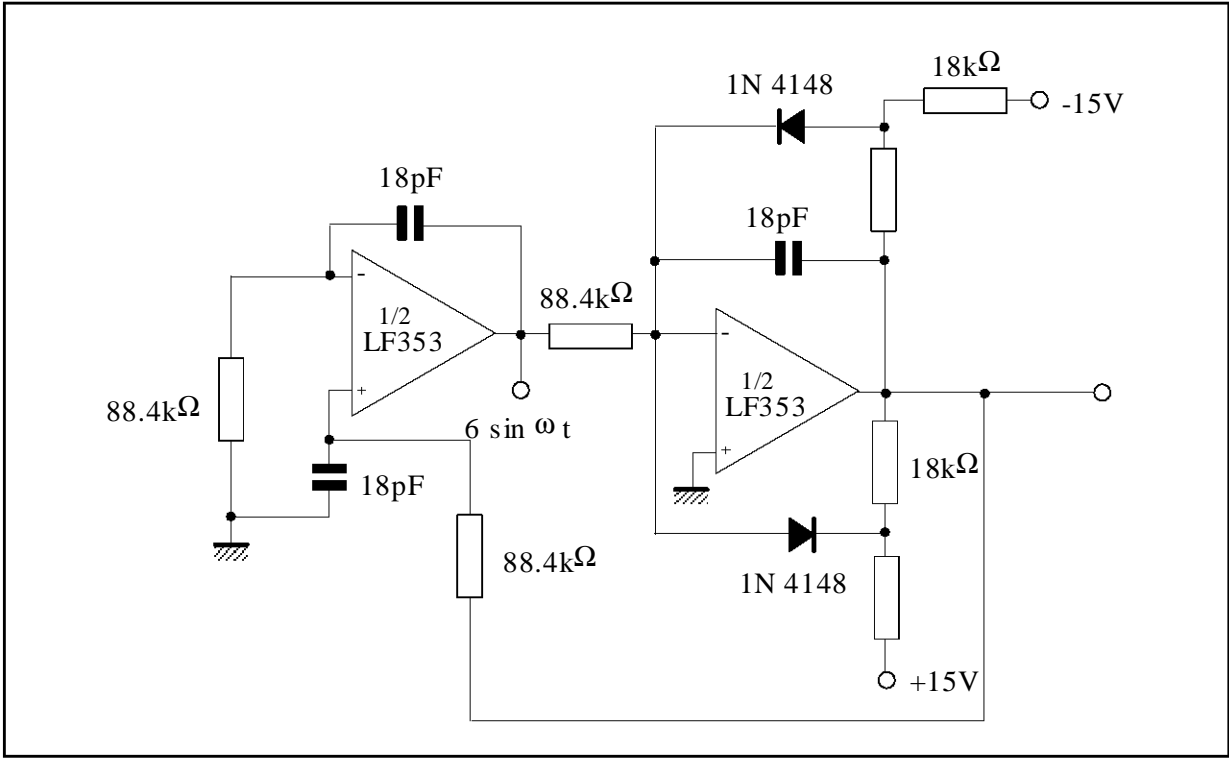


Figure 2 : Gain-of-10 Inverting Amplifier

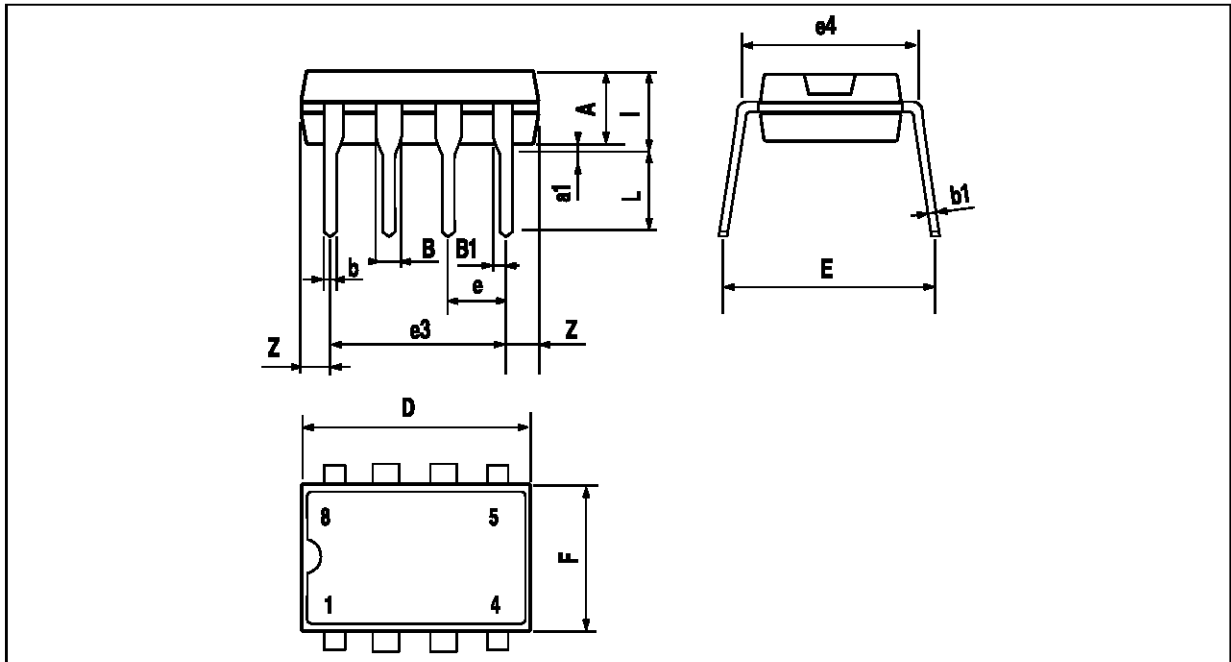


TYPICAL APPLICATIONS

QUADRUPLE OSCILLATOR



PACKAGE MECHANICAL DATA
8 PINS - PLASTIC DIP

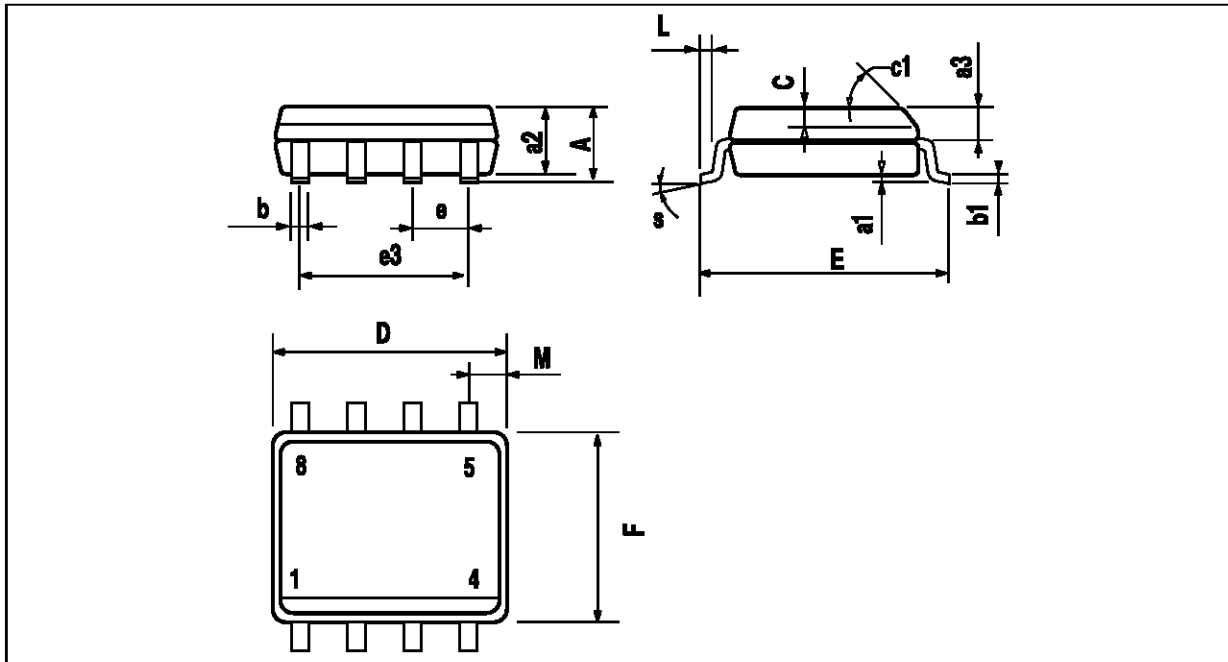


PM-DIP8.EPS

Dimensions	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A		3.32			0.131	
a1	0.51			0.020		
B	1.15		1.65	0.045		0.065
b	0.356		0.55	0.014		0.022
b1	0.204		0.304	0.008		0.012
D			10.92			0.430
E	7.95		9.75	0.313		0.384
e		2.54			0.100	
e3		7.62			0.300	
e4		7.62			0.300	
F			6.6			0.260
i			5.08			0.200
L	3.18		3.81	0.125		0.150
Z			1.52			0.060

DIP8.TBL

PACKAGE MECHANICAL DATA
8 PINS - PLASTIC MICROPACKAGE (SO)



PM-S08.EPS

Dimensions	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A			1.75			0.069
a1	0.1		0.25	0.004		0.010
a2			1.65			0.065
a3	0.65		0.85	0.026		0.033
b	0.35		0.48	0.014		0.019
b1	0.19		0.25	0.007		0.010
C	0.25		0.5	0.010		0.020
c1	45° (typ.)					
D	4.8		5.0	0.189		0.197
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		3.81			0.150	
F	3.8		4.0	0.150		0.157
L	0.4		1.27	0.016		0.050
M			0.6			0.024
S	8° (max.)					

S08.TBL

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